

• General Description

It combines trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- AEC-Q101 Qualified
- Low $R_{DS(ON)}$ to minimize conductive loss
- High GOX reliability
- Low Thermal resistance

• Application

- BLDC Motor driver
- DC-DC
- Battery protection

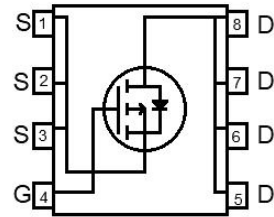
• Ordering Information:

Part NO.	ZMA029P03N
Marking	ZM029P03
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

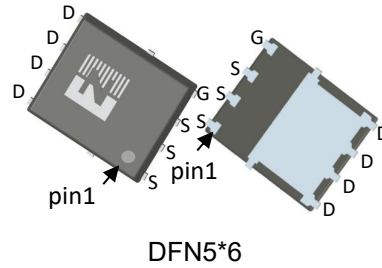
• Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		-30	V
Gate-Source Voltage ^①	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	-120	A
	I_D	$T_C=75^\circ\text{C}$	-99	A
	I_D	$T_C=100^\circ\text{C}$	-85	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^\circ\text{C}$;	-480	A
Total Power Dissipation	P_D	$T_C=25^\circ\text{C}$	107	W
Total Power Dissipation	P_D	$T_A=25^\circ\text{C}$	3.3	W
Operating Junction Temperature	T_J		-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to +175	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	$L=0.1\text{mH}$, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	240	mJ
		$L=0.5\text{mH}$, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	504	mJ
ESD Level (HBM)			CLASS 2	

• Product Summary



$V_{DS} = -30\text{V}$
 $R_{DS(ON)} = 2.9\text{m}\Omega$
 $I_D = -120\text{A}$



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	1.4	°C/W
Thermal resistance, junction-ambient ^②	R_{thJA} ^②		-	45	°C/W
Soldering temperature	T_{sold}		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\mu A$	-1.3	-1.8	-2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS} = 0V, V_{DS} = -30V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -24A$		2.9	3.5	m Ω
		$V_{GS} = -4.5V, I_D = -12A$		4.2	6	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = -5V, I_{SD} = -20A$		20		S
Diode Forward Voltage	V_{FSD}	$V_{GS} = 0V, I_{SD} = -24A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
Input capacitance	C_{iss}	$f = 1MHz, V_{DS} = -25V$	-	10870	-	pF	
Output capacitance	C_{oss}		-	1082	-		
Reverse transfer capacitance	C_{rss}		-	854	-		
Gate Resistance	R_g	$f = 1MHz$	-	3		Ω	
Total gate charge	Q_g	$V_{DD} = -15V, I_D = -20A, V_{GS} = -10V$	-	184	-	nC	
	$Q_g(-4.5V)$		-	83	-		
	Gate - Source charge		Q_{gs}	-	37		-
	Gate - Drain charge		Q_{gd}	-	23		-
Turn-ON Delay time	$t_{D(on)}$	$V_{GS} = -10V, V_{DS} = -15V, R_G = 3.3\Omega, I_D = -20A$	-	27	-	ns	
Turn-ON Rise time	t_r		-	105	-	ns	
Turn-Off Delay time	$t_{D(off)}$		-	98	-	ns	
Turn-Off Fall time	t_f		-	33	-	ns	

Fig.1 Gate-Charge Characteristics

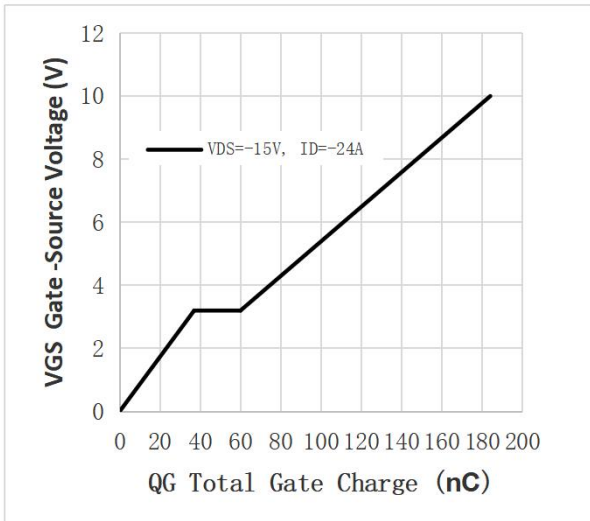


Fig.2 Capacitance Characteristics

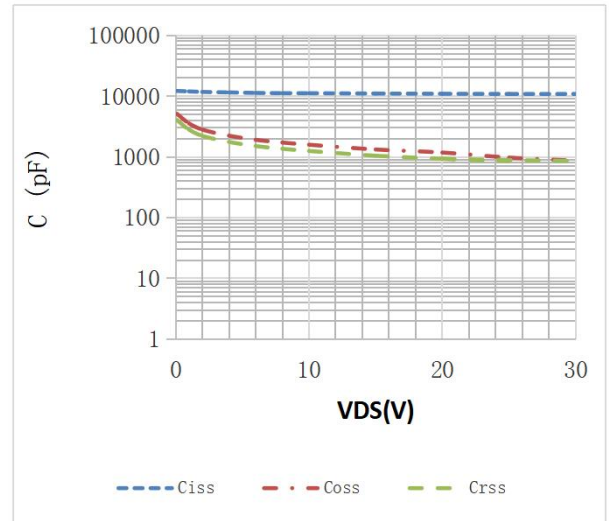


Fig.3 Power Dissipation

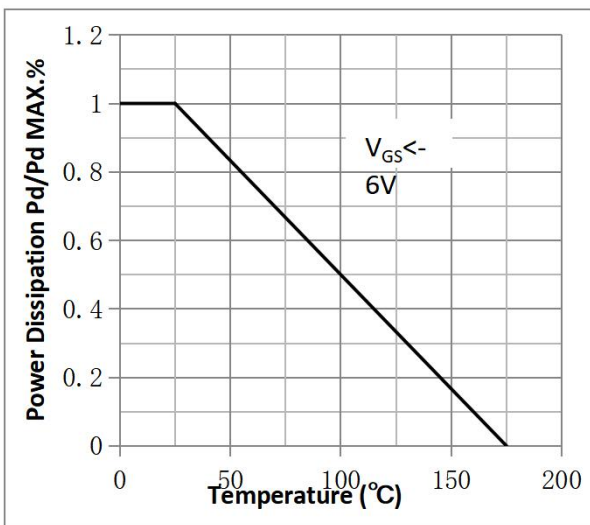


Fig.4 Typical output Characteristics

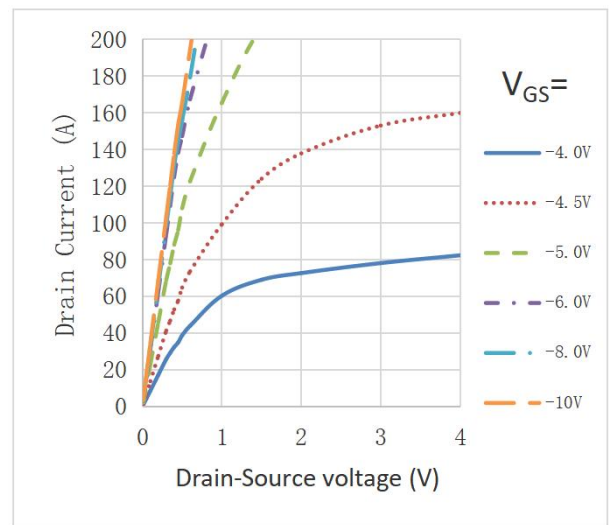


Fig.5 Threshold Voltage V.S Junction Temperature

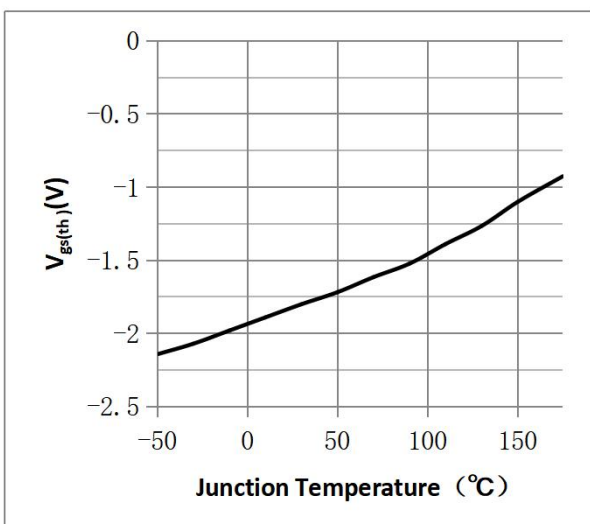


Fig.6 Resistance V.S Drain Current

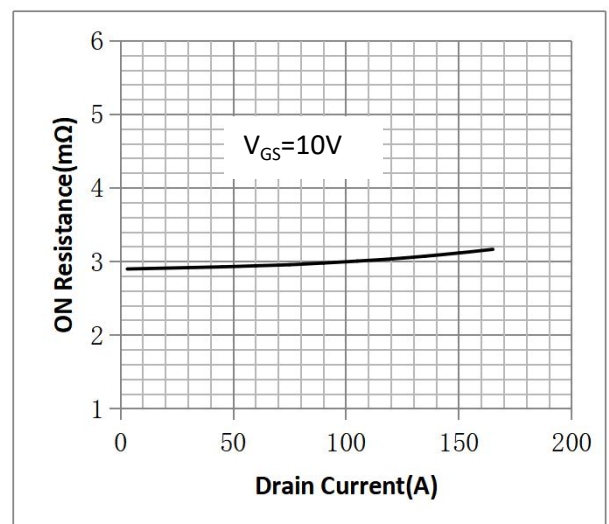


Fig.7 On-Resistance VS Gate Source Voltage

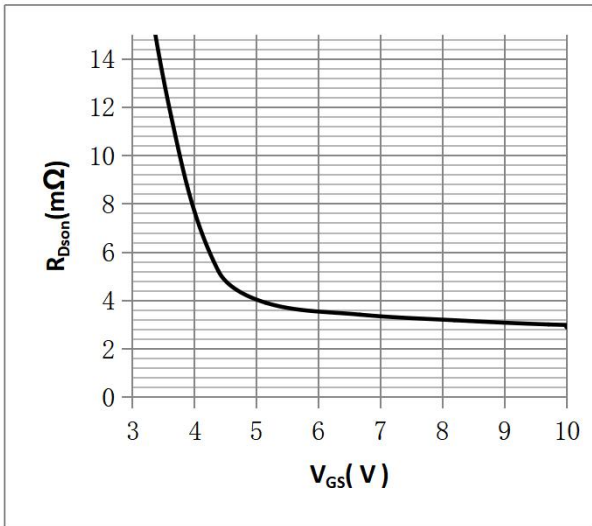


Fig.8 On-Resistance V.S Junction Temperature

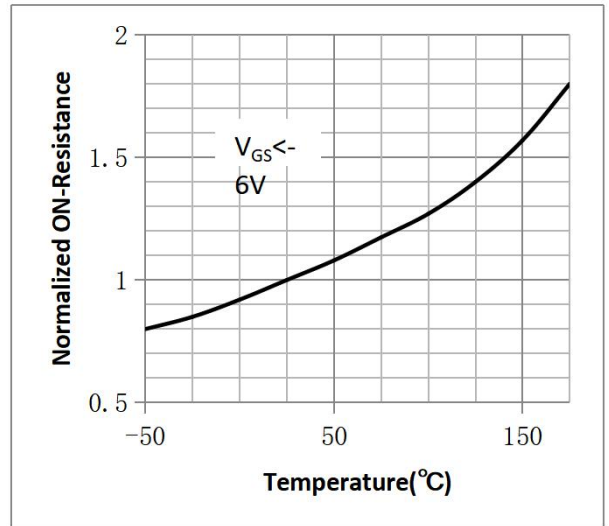


Figure 9. Diode Forward Voltage vs. Current

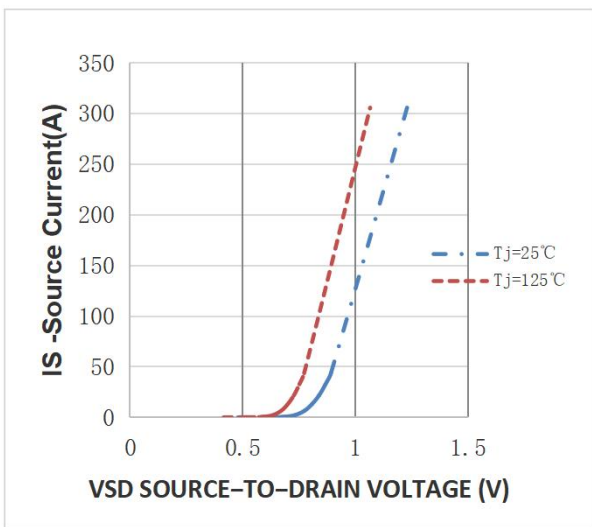


Figure 10. Transfer Characteristics

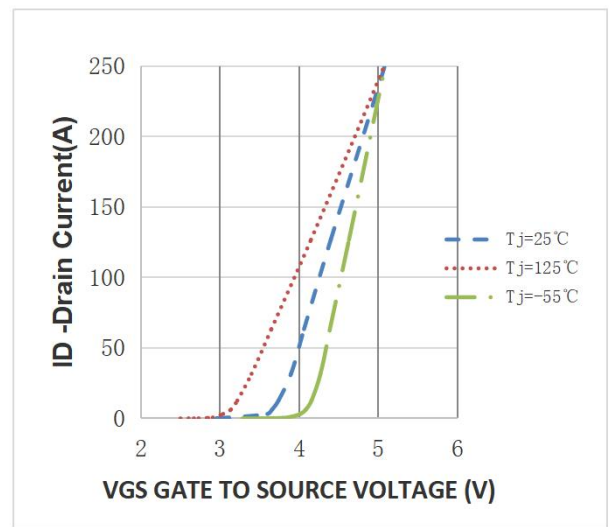


Fig.11 Safe Operating Area

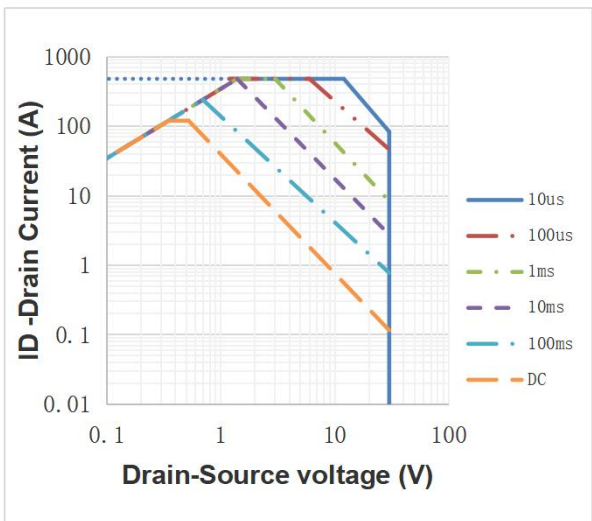
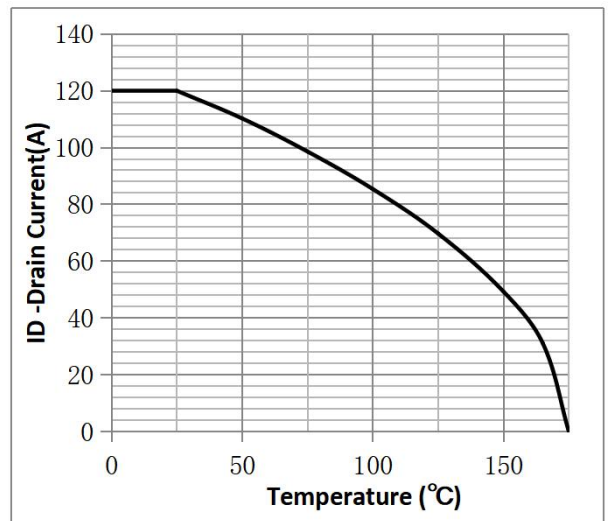
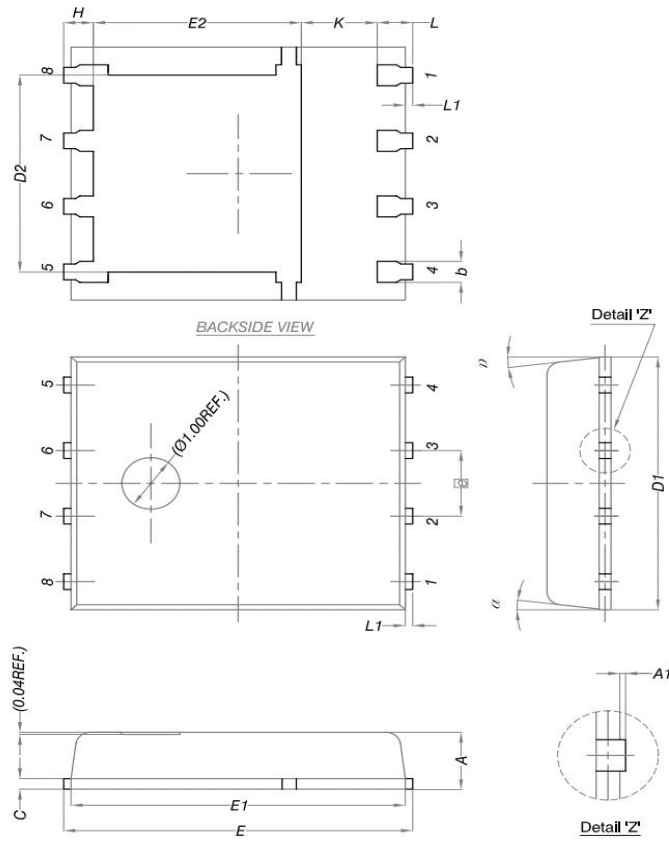


Fig.12 I_D vs. Case Temperature^③



•DFN5*6 Package Outline



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°

Note:

- ① Pulse : $V_{GS}=+20V/-20V$, Duty cycle=50%, $T_j=175^{\circ}C$, $t=1000$ hours; For DC , the following test conditions can be passed: $V_{GS}=-20V/+10V$, $T_j=175^{\circ}C$, $t=1000$ hours;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=-10V$.

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Revision History

Version	Date	Change
A	2021.2.3	NEW
B	2021.11.7	1.Modified Typical output Characteristics curve
C	2022.9.6	1.Add Reach, HF figure 2.Modified ID curve